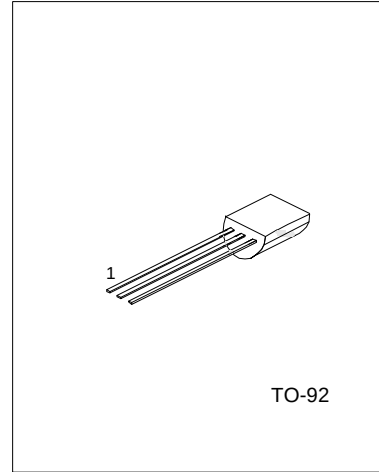


UTC D1616/D1616A NPN PLANAR SILICON TRANSISTOR

NPN EPITAXIAL PLANAR TRANSISTOR

DESCRIPTION

*Audio frequency power amplifier
*Medium speed switching



1:EMITTER 2:COLLECTOR 3: BASE

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Storage Temperature	Tstg	-55 ~+150	°C
Junction Temperature	Tj	150	°C
Total Power Dissipation (Ta=25°C)	Pc	750	mW
Collector to Base Voltage : D1616 D1616A	VCBO	60 120	V
Collector to Emitter Voltage: D1616 D1616A	VCEO	50 60	V
Emitter to Base Voltage	VEBO	6	V
Collector Current	IC	1	A

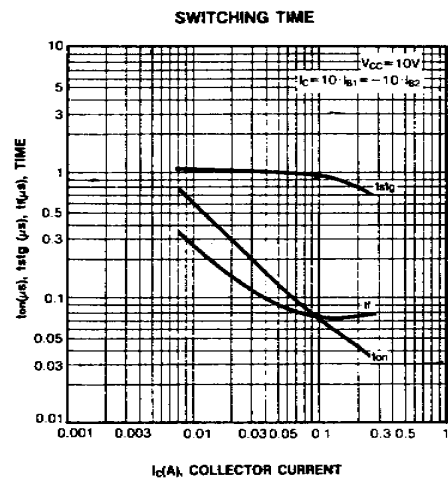
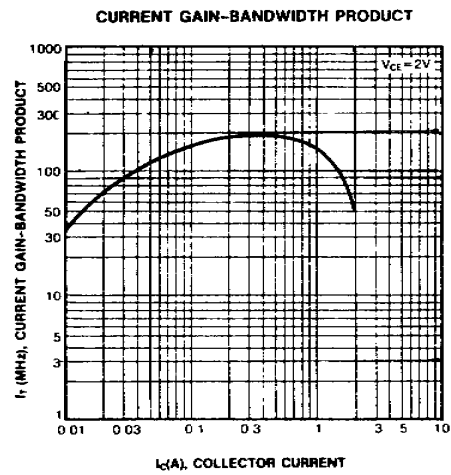
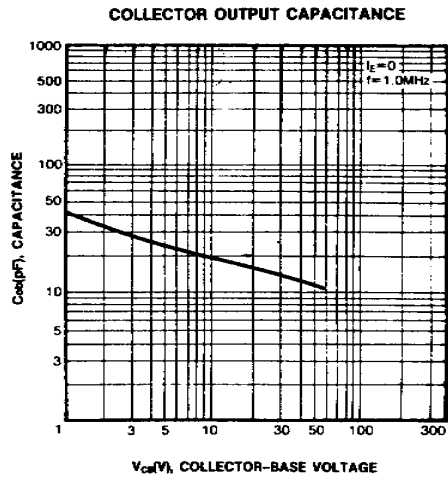
CHARACTERISTICS(Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Collector Cut-Off Current	ICBO	VCB=60V			100	nA
Emitter Cut-Off Current	IEBO	VEB= 6V			100	nA
Collector-Emitter Saturation Voltage	VCE(SAT)	IC=1A, IB=50mA		0.15	0.3	V
Base-Emitter Saturation Voltage	VBE(SAT)	IC=1A, IB=50mA		0.9	1.2	V
Base Emitter On Voltage	VBE(ON)	VCE=2V, IC=50mA	600	640	700	mV
DC Current Gain: D1616 D1616A	hFE1	VCE=2V, IC=100mA	135 135		600 400	
	hFE2	VCE=2V, IC=1A	81			
Current Gain Bandwidth Product	fT	VCE=2V, IC=100mA	100	160		MHz
Output Capacitance	Cob	VCB=10V, f=1MHz			19	pF
Turn On Time	ton	VCE=10V, IC=100mA		0.07		us
Storage Time	ts	IB1=-IB2=10mA		0.95		us
Fall Time	tf	VBE(off)=-2i -3V		0.07		us

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Classification of hFE

RANK	Y	G	L
hFE1	135-270	200-400	300-600



UTC D1616/D1616A NPN PLANAR SILICON TRANSISTOR

